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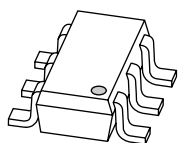
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Kind regards,

Team Nexperia



PMD9001D

MOSFET driver

Rev. 01 — 16 November 2006

Product data sheet

1. Product profile

1.1 General description

NPN Resistor-Equipped Transistor (RET), NPN general-purpose transistor and high-speed switching diode connected in totem pole configuration in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Two transistors and one high-speed switching diode as driver
- Totem pole configuration
- Application-optimized pinout
- Internal connections to minimize layout effort
- Space-saving solution
- Reduces component count

1.3 Applications

- MOSFET driver

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
I_C	collector current		-	-	0.1	A
Transistor 2 (TR2)						
V_{CEO}	collector-emitter voltage	open base	-	-	45	V
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	0.2	A
Diode (D1)						
I_F	forward current		-	-	-0.2	A
V_F	forward voltage	$I_F = -200$ mA	^[1] -	-	-1.1	V

[1] Pulse test: $t_p \leq 300$ μ s; $\delta \leq 0.02$.

2. Pinning information

Table 2. Pinning

Pin	Symbol	Description	Simplified outline	Symbol
1	OUT	output		
2	GND	ground		
3	IN	input		
4	RC	collector resistor		
5	RC	collector resistor		
6	VCC	supply voltage		

006aaa658

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMD9001D	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457

4. Marking

Table 4. Marking codes

Type number	Marking code
PMD9001D	9B

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Transistor 1 (TR1)					
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	10	V
I_C	collector current		-	0.1	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1\text{ ms}$	-	0.1	A
V_I	input voltage				
	positive		-	+12	V
	negative		-	-10	V
Transistor 2 (TR2)					
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	45	V

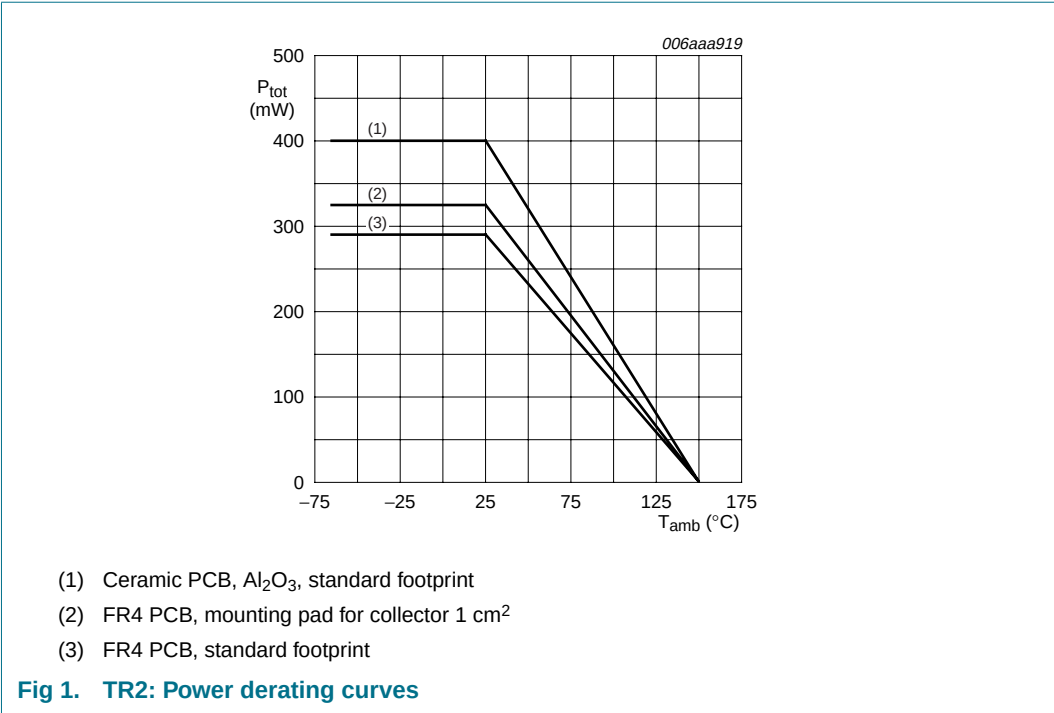
Table 5. Limiting values ...continued*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit
I _C	collector current		-	0.1	A
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	0.2	A
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms	-	0.2	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] -	290	mW
			[2] -	325	mW
			[3] -	400	mW
Diode (D1)					
I _F	forward current		-	−0.2	A
I _{FRM}	repetitive peak forward current	t _p ≤ 1 ms; δ ≤ 0.25	-	−0.6	A
I _{FSM}	non-repetitive peak forward current	square wave			
		t _p = 1 μs	-	−9	A
		t _p = 100 μs	-	−3	A
		t _p = 10 ms	-	−1.7	A
Device					
T _j	junction temperature		-	150	°C
T _{amb}	ambient temperature		−65	+150	°C
T _{stg}	storage temperature		−65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

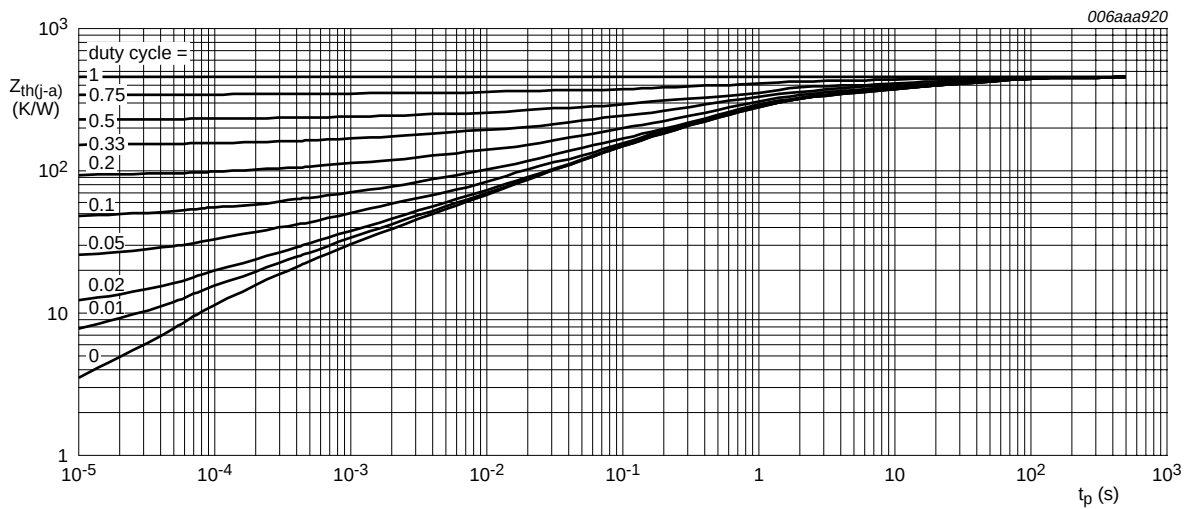


6. Thermal characteristics

Table 6. Thermal characteristics

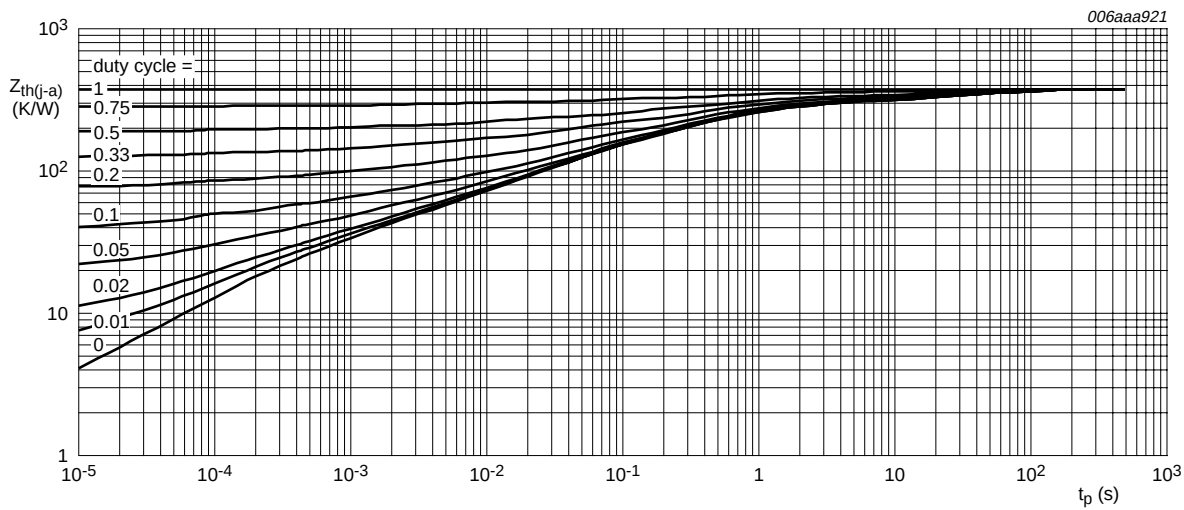
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Transistor 2 (TR2)						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1] -	-	430	K/W
			[2] -	-	385	K/W
			[3] -	-	312	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



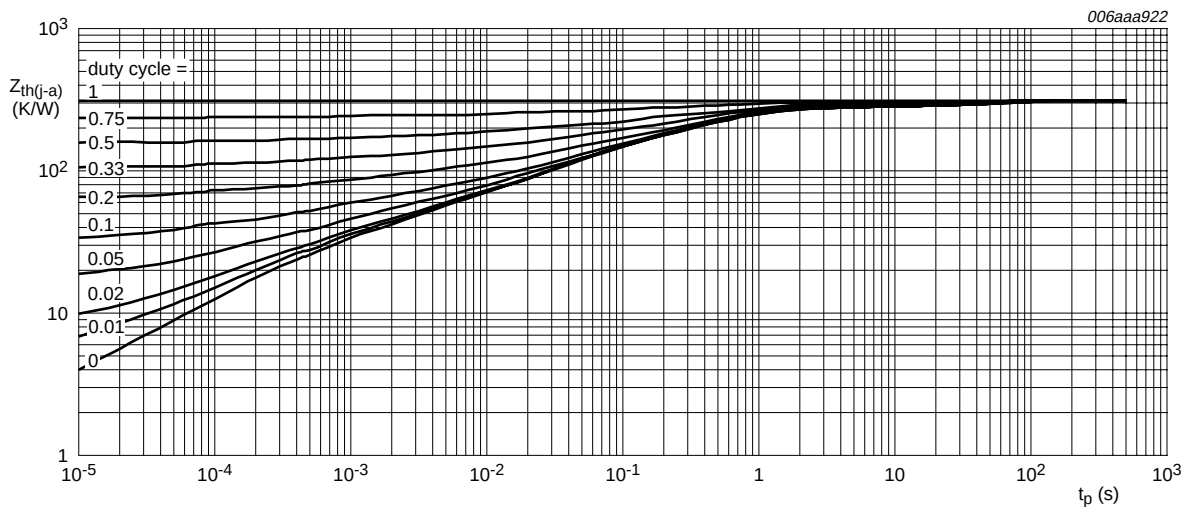
FR4 PCB, standard footprint

Fig 2. TR2: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 1 cm²

Fig 3. TR2: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al₂O₃, standard footprint

Fig 4. TR2: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

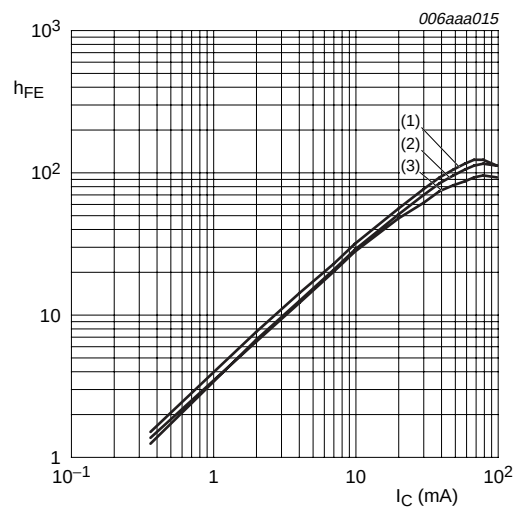
Table 7. Characteristics
T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Transistor 1 (TR1)						
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A	-	-	100	nA
I _{CEO}	collector-emitter cut-off current	V _{CE} = 30 V; I _E = 0 A	-	-	1	μA
		V _{CE} = 30 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _E = 0 A	-	-	2	mA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 20 mA	30	55	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 10 mA; I _B = 0.5 mA	-	60	150	mV
V _{I(off)}	off-state input voltage	V _{CE} = 5 V; I _C = 0.1 mA	-	1.1	0.5	V
V _{I(on)}	on-state input voltage	V _{CE} = 0.3 V; I _C = 20 mA	2	1.6	-	V
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	
Transistor 2 (TR2)						
I _{CBO}	collector-base cut-off current	V _{CB} = 30 V; I _E = 0 A	-	-	15	nA
		V _{CB} = 30 V; I _E = 0 A; T _j = 150 °C	-	-	5	μA
V _{CEsat}	collector-emitter saturation voltage	I _C = 10 mA; I _B = 0.5 mA	-	60	200	mV
		I _C = 100 mA; I _B = 5 mA	-	200	400	mV
		I _C = 200 mA; I _B = 20 mA	-	340	500	mV

Table 7. Characteristics ...continued $T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified.

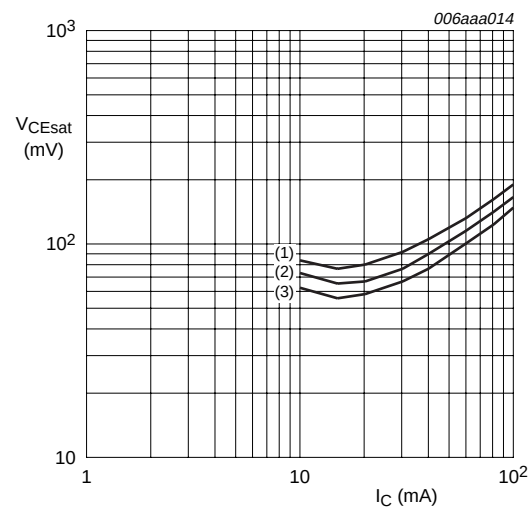
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{BEsat}	base-emitter saturation voltage	I _C = 10 mA; I _B = 0.5 mA	-	0.7	-	V
		I _C = 100 mA; I _B = 5 mA	-	0.9	-	V
V _{BE}	base-emitter voltage	V _{CE} = 5 V; I _C = 2 mA	610	660	710	mV
		V _{CE} = 5 V; I _C = 10 mA	-	-	770	mV
Diode (D1)						
V _F	forward voltage	I _F = −200 mA	[1] -	-	−1.1	V
TR2 and D1						
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 1 mA	200	290	450	
		V _{CE} = 5 V; I _C = 100 mA	95	140	-	
		V _{CE} = 5 V; I _C = 200 mA	24	35	-	
Device						
t _d	delay time	I _C = 0.05 A; I _B = 2.5 mA	-	11	-	ns
t _r	rise time		-	54	-	ns
t _{on}	turn-on time		-	65	-	ns
t _s	storage time		-	1100	-	ns
t _f	fall time		-	207	-	ns
t _{off}	turn-off time		-	1307	-	ns

[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.



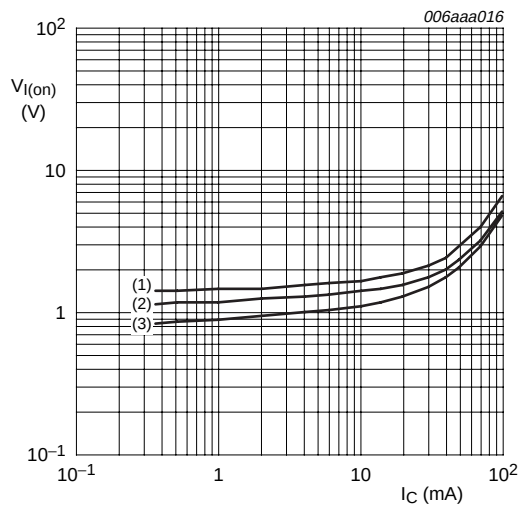
- $V_{CE} = 5\text{ V}$
(1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = -40\text{ }^{\circ}\text{C}$

Fig 5. TR1: DC current gain as a function of collector current; typical values



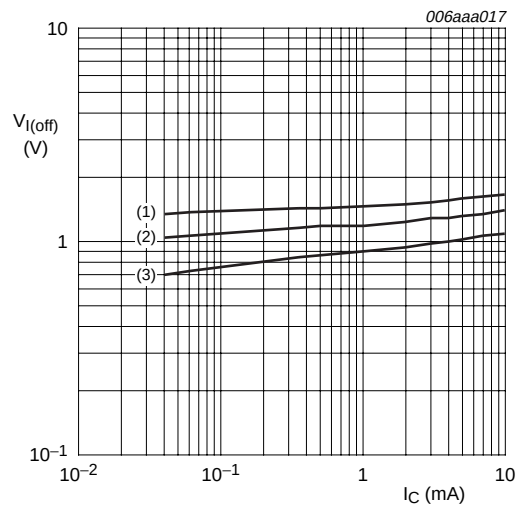
- $I_C/I_B = 20$
(1) $T_{amb} = 100\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = -40\text{ }^{\circ}\text{C}$

Fig 6. TR1: Collector-emitter saturation voltage as a function of collector current; typical values



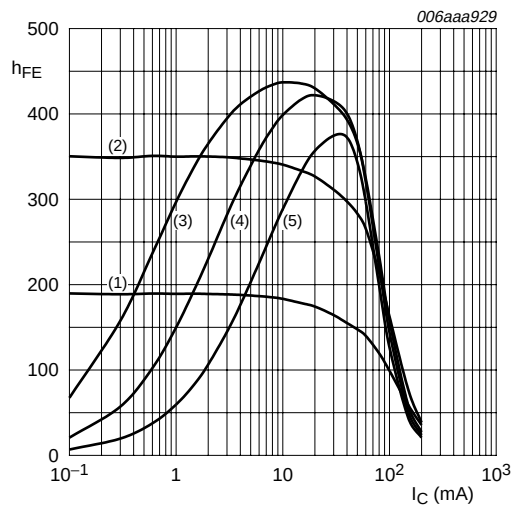
- $V_{CE} = 0.3\text{ V}$
(1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = 100\text{ }^{\circ}\text{C}$

Fig 7. TR1: On-state input voltage as a function of collector current; typical values



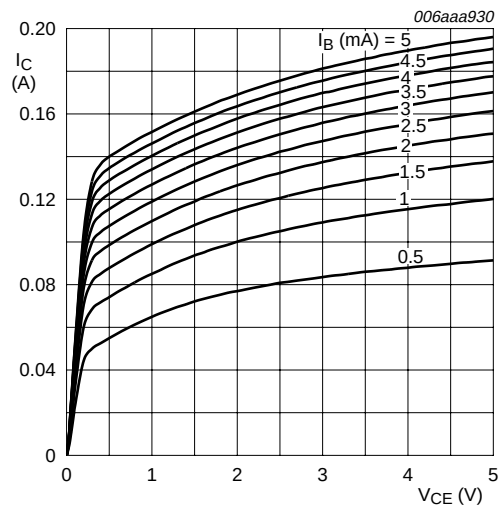
- $V_{CE} = 5\text{ V}$
(1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = 100\text{ }^{\circ}\text{C}$

Fig 8. TR1: Off-state input voltage as a function of collector current; typical values



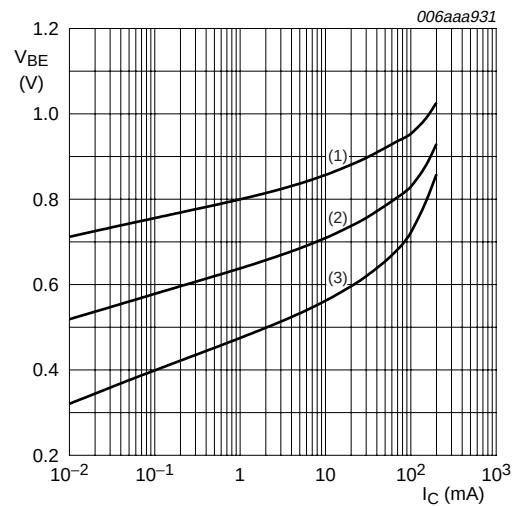
- $V_{CE} = 5\text{ V}$
- (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
 - (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 - (3) $T_{amb} = 100\text{ }^{\circ}\text{C}$
 - (4) $T_{amb} = 125\text{ }^{\circ}\text{C}$
 - (5) $T_{amb} = 150\text{ }^{\circ}\text{C}$

Fig 9. TR2 and D1: DC current gain as a function of collector current; typical values



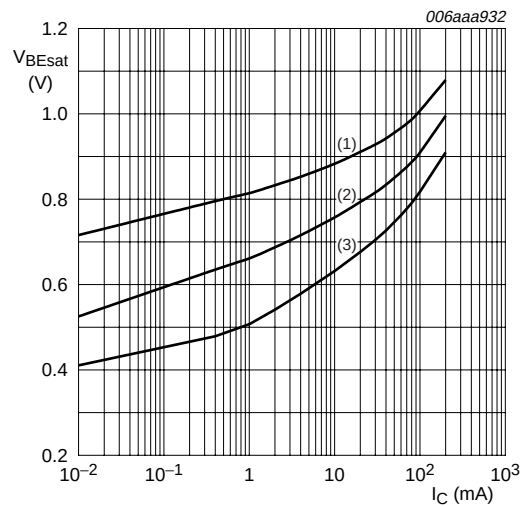
$T_{amb} = 25\text{ }^{\circ}\text{C}$

Fig 10. TR2: Collector current as a function of collector-emitter voltage; typical values



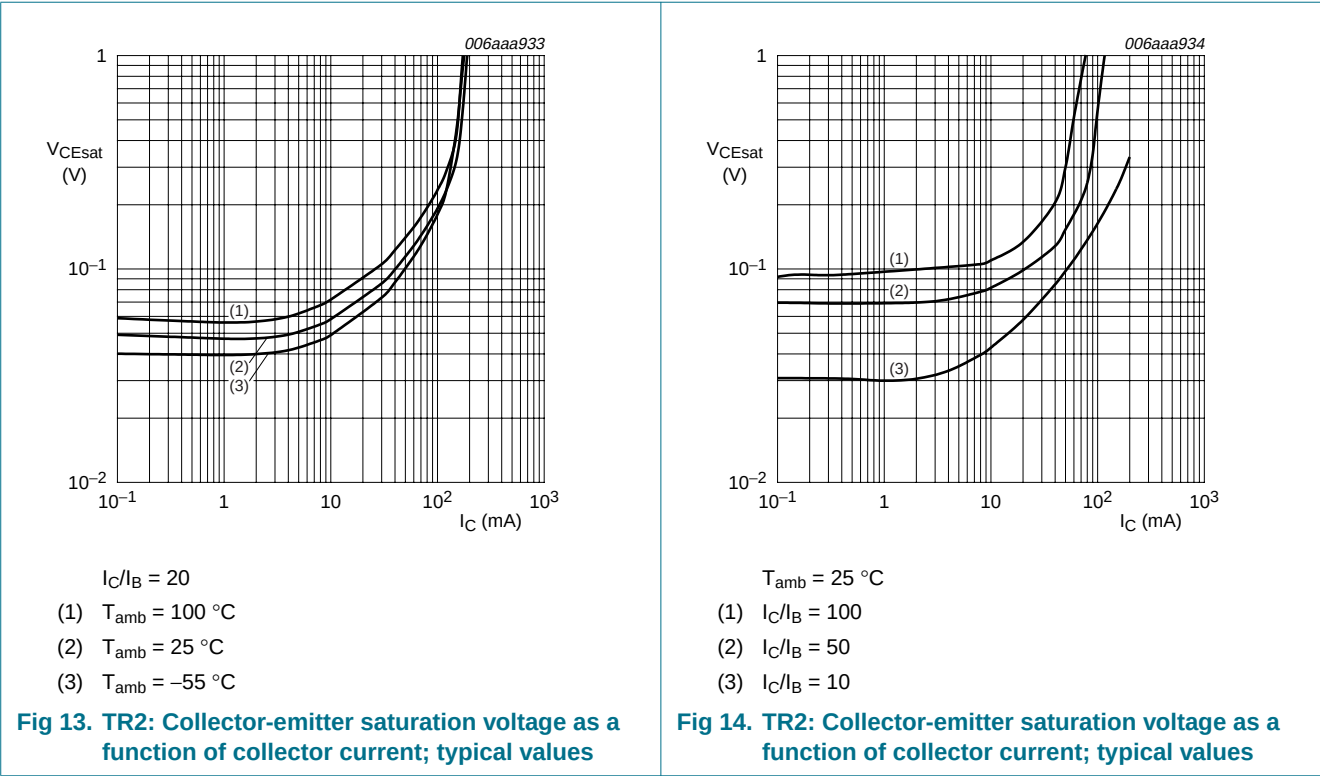
- $V_{CE} = 5\text{ V}$
- (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
 - (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 - (3) $T_{amb} = 100\text{ }^{\circ}\text{C}$

Fig 11. TR2: Base-emitter voltage as a function of collector current; typical values

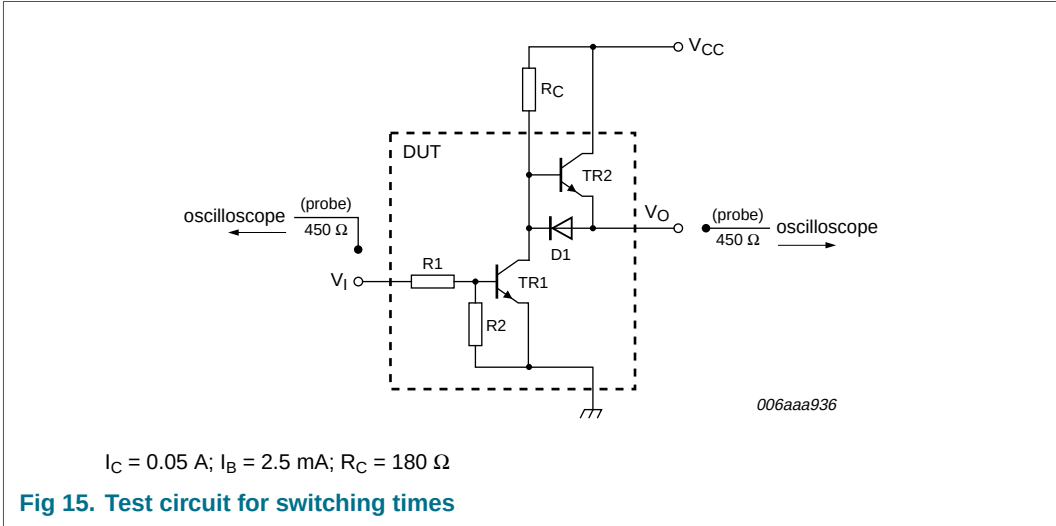


- $I_C/I_B = 20$
- (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
 - (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 - (3) $T_{amb} = 100\text{ }^{\circ}\text{C}$

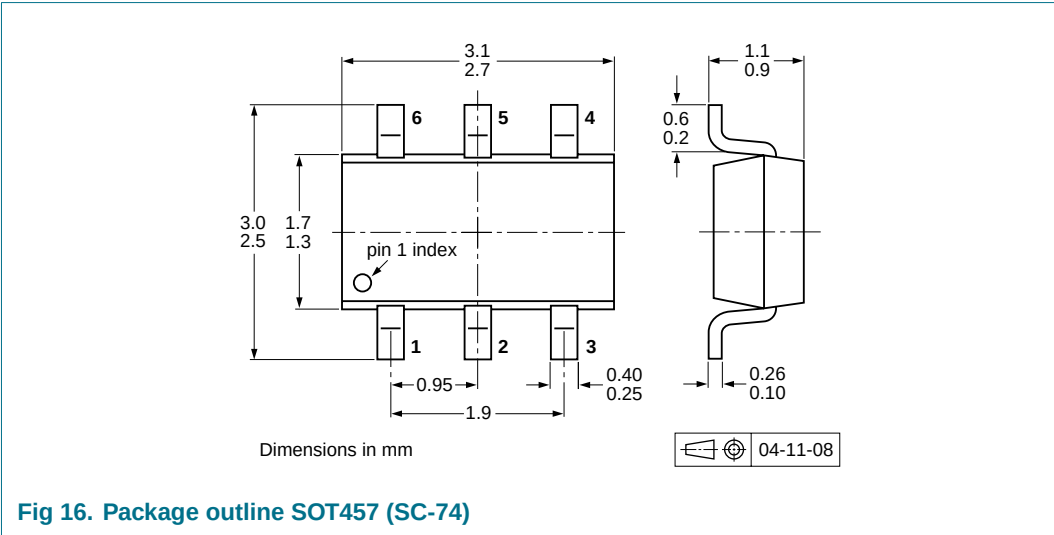
Fig 12. TR2: Base-emitter saturation voltage as a function of collector current; typical values



8. Test information



9. Package outline



10. Packing information

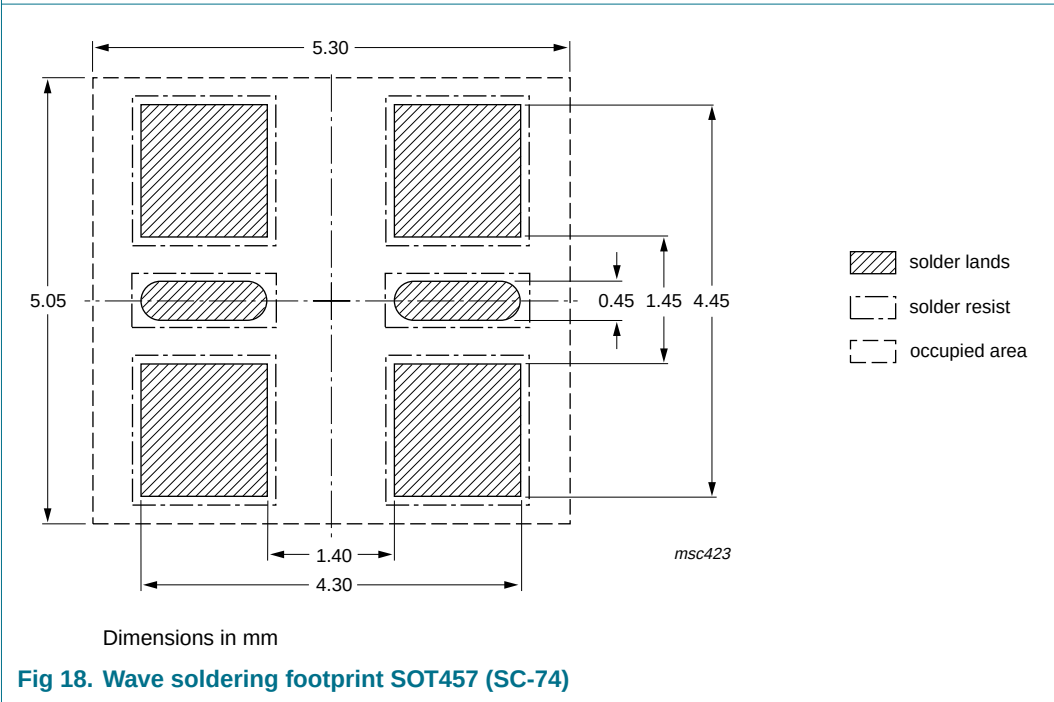
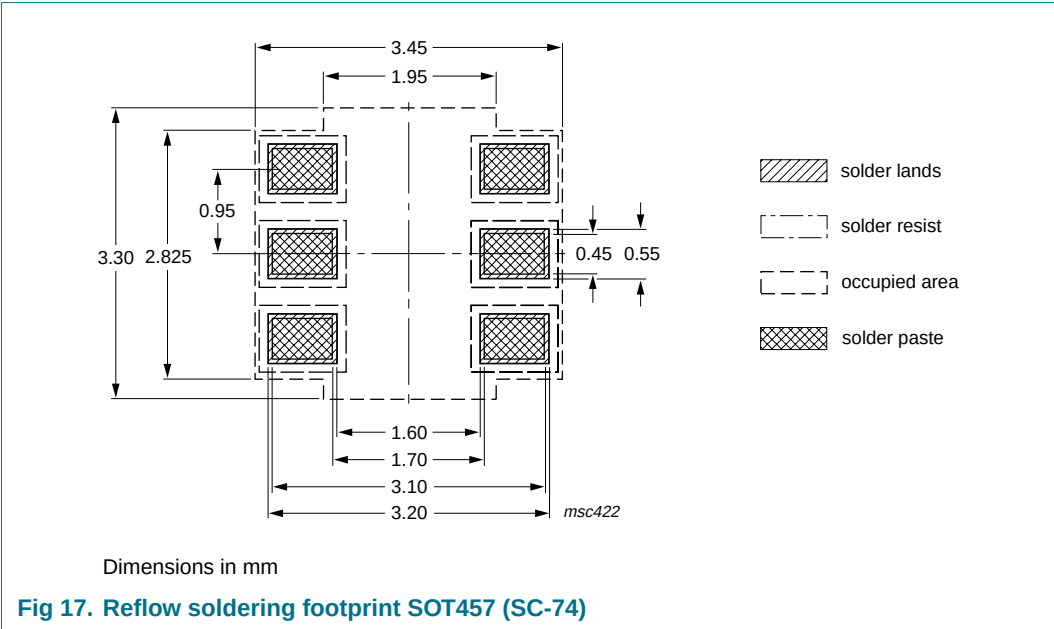
Table 8. Packing methods					
The indicated -xxx are the last three digits of the 12NC ordering code. ^[1]					
Type number	Package	Description		Packing quantity	
				3000	10000
PMD9001D	SOT457	4 mm pitch, 8 mm tape and reel; T1 ^[2]	-115	-135	
		4 mm pitch, 8 mm tape and reel; T2 ^[3]	-125	-165	

[1] For further information and the availability of packing methods, see [Section 14](#).

[2] T1: normal taping

[3] T2: reverse taping

11. Soldering



12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMD9001D_1	20061116	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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